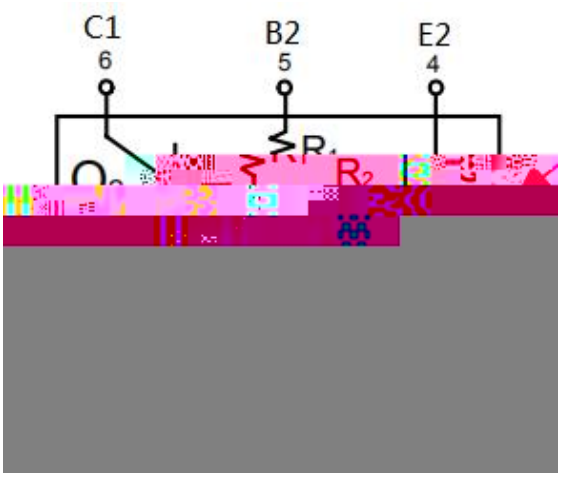
修订记录 / Revised record

A	2020.08.21		LRC-LMUN5314DW1T1G		
B	2021-11-25	6			

SOT-363 NPN+PNP
Double silicon NPN and PNP transistor in a SOT-363 Plastic Package

With built-in bias resistors, simplify circuit design, reduce a quantity of parts and manufacturing process, Halogen-free Product.

Switching applications, interface circuit and driver circuit applications.



放大及印章代码 / h_{FE} Classifications & Marking

Marking H314

Parameter	Symbol	Rating	Unit
Output Voltage	V_{CC}	50	V
Input Voltage	V_{IN}	40	V
		-6	V
Output Current	I_C	100	mA
	I_O	70	mA
Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	C
Storage Temperature Range	T_{stg}	-55～150	C

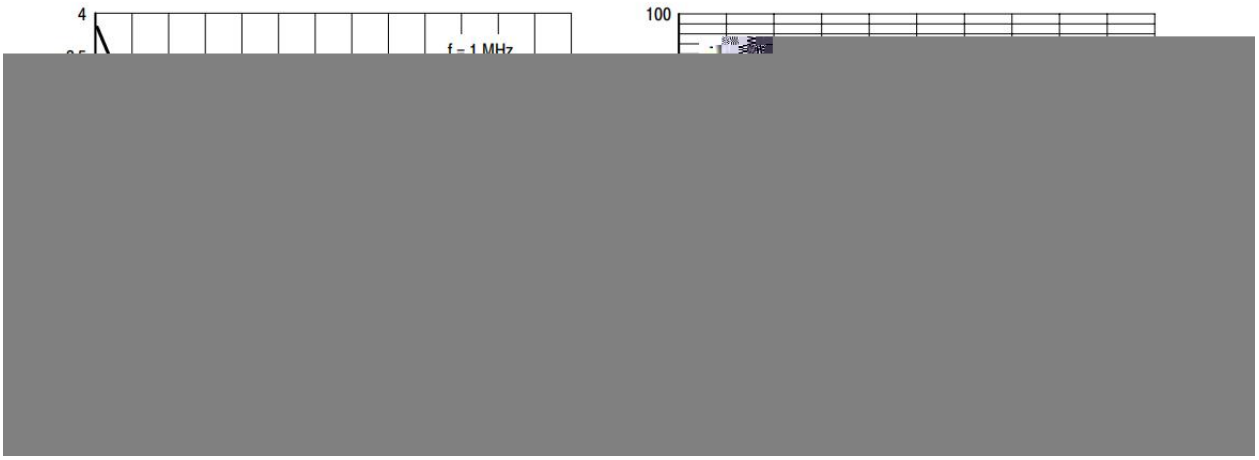
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Voltage(OFF)	$V_{I(off)}$	v_{CC}=5.0V I_O=100μA			0.3	V
Input Voltage(ON)	$V_{I(on)}$	V_O=0.3V I_O=1mA	1.4			V
Output Voltage	$V_{O(on)}$	I_O =5mA I_I=0.25mA		0.1	0.3	V

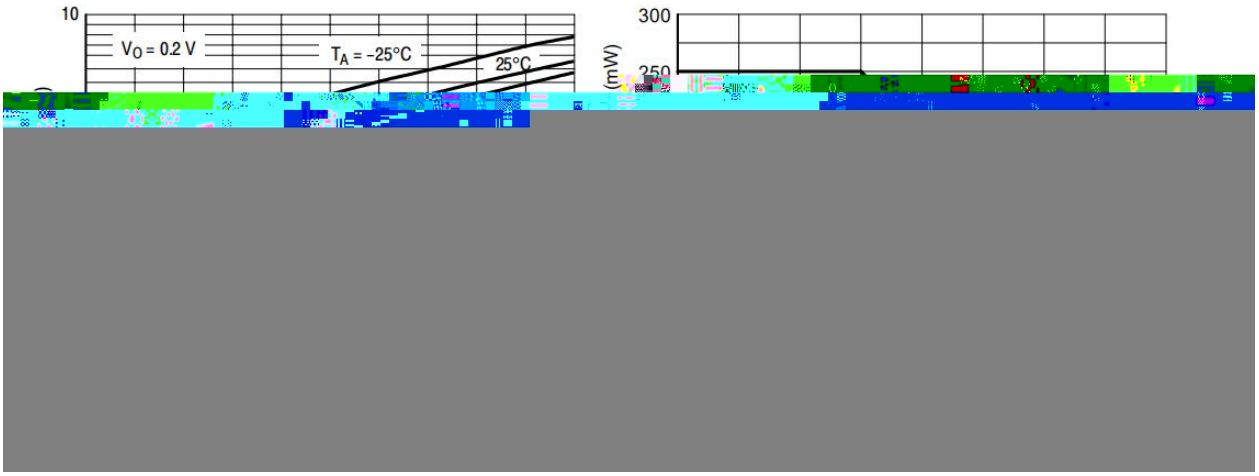
I

BRMUN5314WS

电参数曲线图 / Electrical Characteristic Curve(NPN)







BRMUN5314WS
Rev.B Nov.-2021

BRMUN5314WS
Rev.B Nov.-2021

印章说明 / Marking Instructions

H314**
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● “1”

H314

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Note:

● “1” Pin

H314 Product Type Code

***: Lot No. Code, code change with Lot No.